

SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

CPH3431 — General-Purpose Switching Device **Applications**

Features

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		200	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		0.6	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	2.4	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)	1.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Uill
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	200			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =200V, V _{GS} =0V			10	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =300mA	0.6	1		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =300mA, V _{GS} =10V		1.8	2.4	Ω
	RDS(on)2	ID=300mA, VGS=4V		2.0	2.8	Ω
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		340		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		16		pF
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		10		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		10		ns
Rise Time	t _r	See specified Test Circuit.		4		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		35		ns
Fall Time	tf	See specified Test Circuit.		27		ns

Marking: ZG Continued on next page.

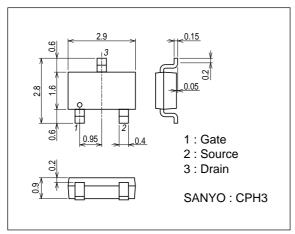
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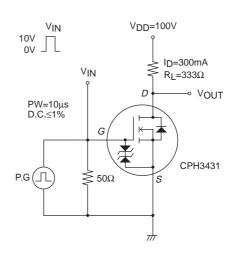
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	J Gill
Total Gate Charge	Qg	V _D S=100V, V _G S=10V, I _D =600mA		7		nC
Gate-to-Source Charge	Qgs	V _{DS} =100V, V _{GS} =10V, I _D =600mA		1		nC
Gate-to-Drain "Miller" Charge	Qgd	VDS=100V, VGS=10V, ID=600mA		0.8		nC
Diode Forward Voltage	VSD	IS=600mA, VGS=0V		0.79	1.2	V

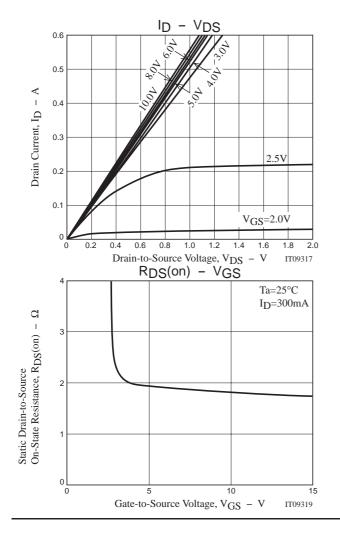
Package Dimensions

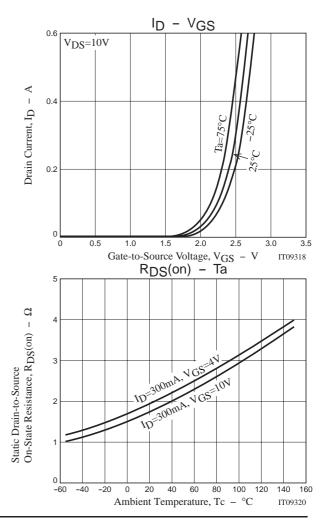
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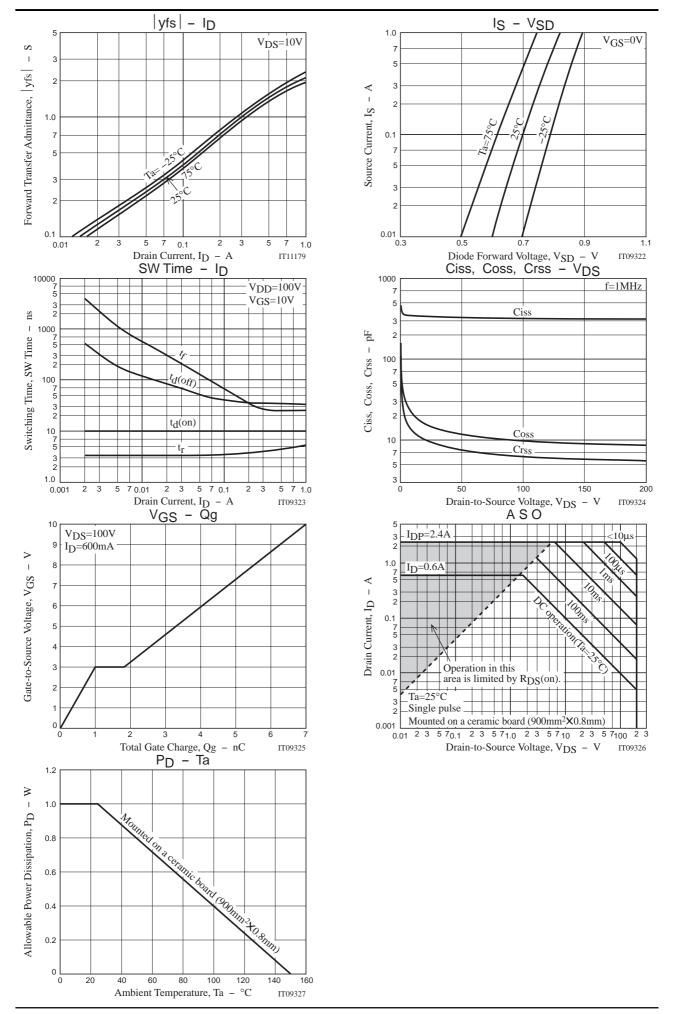


Switching Time Test Circuit









Note on usage: Since the CPH3431 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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